

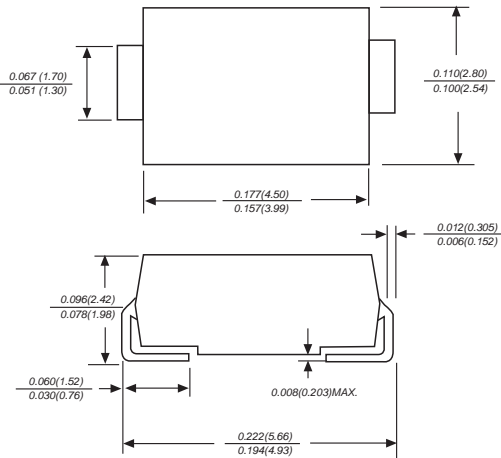


# SS12 THRU SS1200

## SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts Forward Current - 1.0 Ampere

### DO-214AC/SMA



### FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Metal silicon junction, majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed: 250°C/10 seconds at terminals

### MECHANICAL DATA

**Case:** JEDEC DO-214AC molded plastic body  
**Terminals:** leads solderable per MIL-STD-750, Method 2026  
**Polarity:** Color band denotes cathode end  
**Mounting Position:** Any  
**Weight:** 0.002 ounce, 0.07 grams

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.  
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

MDD Catalog Number	SYMBOLS	SS12	SS13	SS14	SS15	SS16	SS18	SS110	SS1150	SS1200	UNITS	
Marking code		MDD SS12	MDD SS13	MDD SS14	MDD SS15	MDD SS16	MDD SS18	MDD SS110	MDD SS1150	MDD SS1200		
Maximum repetitive peak reverse voltage	$V_{RRM}$	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum RMS voltage	$V_{RMS}$	14	21	28	35	42	56	70	105	140	VOLTS	
Maximum DC blocking voltage	$V_{DC}$	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum average forward rectified current at $T_L$ (see fig.1)	$I_{(AV)}$	1.0									Amp	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	30.0									Amps	
Maximum instantaneous forward voltage at 1.0A	$V_F$	0.45	0.55	0.70			0.85		0.95		Volts	
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	$I_R$	0.5					0.2				mA	
Typical junction capacitance (NOTE 1)	$C_J$	110			90						pF	
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	88.0									$^\circ\text{C}/\text{W}$	
Operating junction temperature range	$T_J$	-50 to +125					-50 to +150					$^\circ\text{C}$
Storage temperature range	$T_{STG}$	-50 to +150									$^\circ\text{C}$	

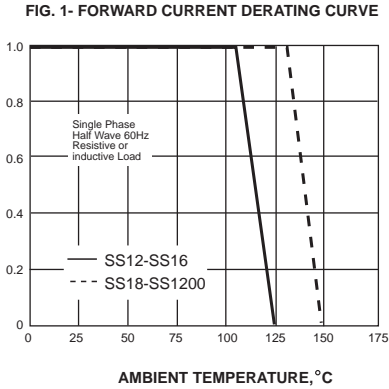
**Note:** 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.  
 2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas



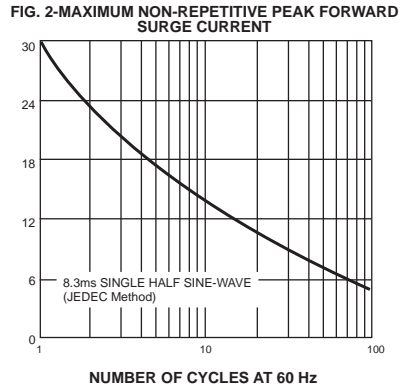
www.microdiode.com

# RATINGS AND CHARACTERISTIC CURVES SS12 THRU SS1200

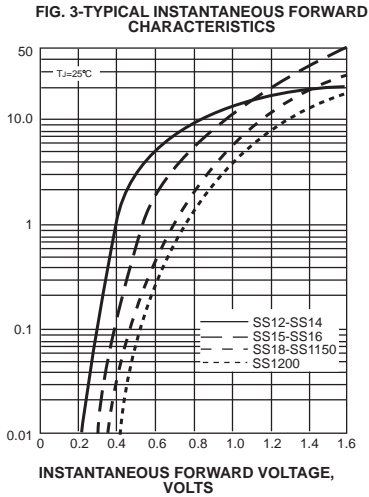
AVERAGE FORWARD RECTIFIED CURRENT,  
AMPERES



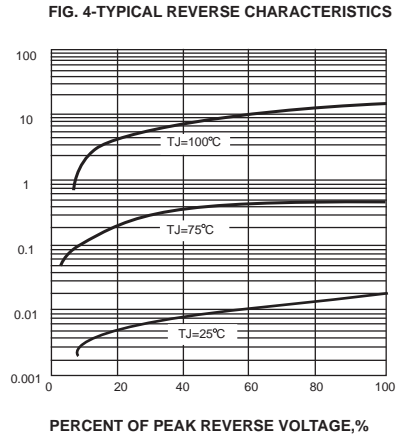
PEAK FORWARD SURGE CURRENT,  
AMPERES



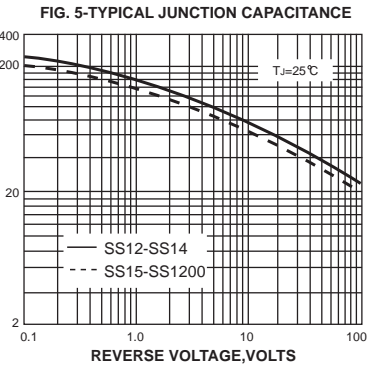
INSTANTANEOUS FORWARD CURRENT, AMPERES



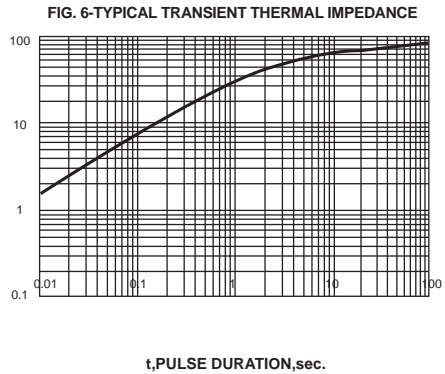
INSTANTANEOUS REVERSE CURRENT,  
MILLIAMPERES



JUNCTION CAPACITANCE, pF



TRANSIENT THERMAL IMPEDANCE,  
°C/W



The cruve graph is for reference only, can't be the basis for judgment(曲线图仅供参考)!

